

ABSTRACT OF THE DISCLOSURE

A method of forming a non-single-crystalline capacitor in an integrated circuit. It includes the steps of forming a first non-single-crystalline layer on a gate dielectric layer of a substrate of an integrated circuit. Next, a capacitor dielectric layer is formed on the first non-single-crystalline layer, and a second non-single-crystalline layer is formed on the capacitor dielectric layer. Portions of the second non-single-crystalline layer are removed to define a top plate of the capacitor. Portions of the capacitor dielectric layer are removed to define a dielectric of the capacitor. Also, portions of the first non-single-crystalline layer are removed to define the bottom plate of the capacitor.